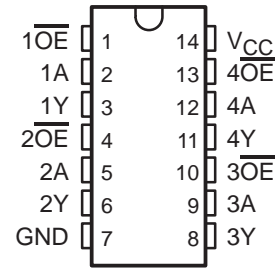


- **EPIC™** (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

D, DGV, OR PW PACKAGE
(TOP VIEW)



description

This quadruple bus buffer gate is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVC125 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (\overline{OE}) input is high.

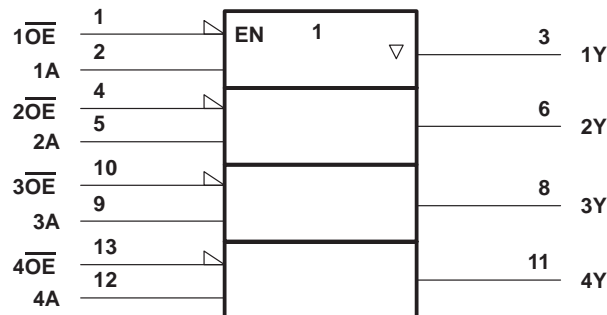
To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC125 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE
(each buffer)

INPUTS		OUTPUT
\overline{OE}	A	Y
L	H	H
L	L	L
H	X	Z

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



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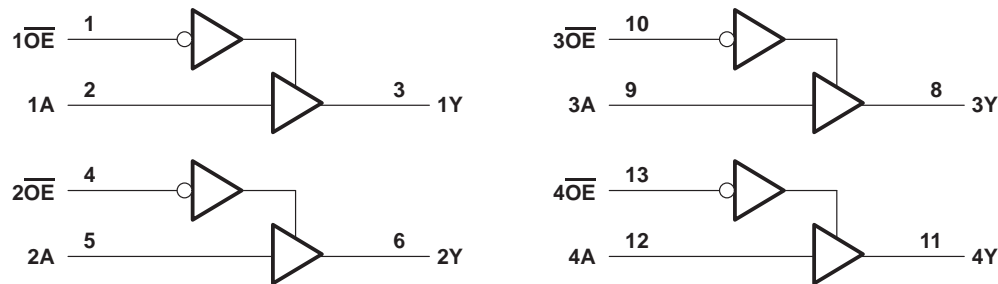
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SN74ALVC125
QUADRUPLE BUS BUFFER GATE
WITH 3-STATE OUTPUTS

SCES110D – JULY 1997 – REVISED DECEMBER 1998

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	–0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	–0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2)	–0.5 V to $V_{CC} + 0.5$ V
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I_{OK} ($V_O < 0$)	–50 mA
Continuous output current, I_O	±50 mA
Continuous current through V_{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3):	
D package	127°C/W
DGV package	182°C/W
PW package	170°C/W
Storage temperature range, T_{stg}	–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		1.65	3.6	V
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 2.7 V to 3.6 V	2		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	0.7		
		V _{CC} = 2.7 V to 3.6 V	0.8		
V _I	Input voltage		0	V _{CC}	V
V _O	Output voltage		0	V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 1.65 V	−4		mA
		V _{CC} = 2.3 V	−12		
		V _{CC} = 2.7 V	−12		
		V _{CC} = 3 V	−24		
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4		mA
		V _{CC} = 2.3 V	12		
		V _{CC} = 2.7 V	12		
		V _{CC} = 3 V	24		
T _A	Operating free-air temperature		−40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

SN74ALVC125

QUADRUPLE BUS BUFFER GATE

WITH 3-STATE OUTPUTS

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
V _{OH}		I _{OH} = –100 µA	1.65 V to 3.6 V	V _{CC} –0.2			V
		I _{OH} = –4 mA	1.65 V	1.2			
		I _{OH} = –6 mA	2.3 V	2			
		I _{OH} = –12 mA	2.3 V	1.7			
			2.7 V	2.2			
			3 V	2.4			
		I _{OH} = –24 mA	3 V	2			
V _{OL}		I _{OL} = 100 µA	1.65 V to 3.6 V	0.2			V
		I _{OL} = 4 mA	1.65 V	0.45			
		I _{OL} = 6 mA	2.3 V	0.4			
		I _{OL} = 12 mA	2.3 V	0.7			
			2.7 V	0.4			
		I _{OL} = 24 mA	3 V	0.55			
I _I		V _I = V _{CC} or GND	3.6 V	±5			µA
I _{OZ}		V _O = V _{CC} or GND	3.6 V	±10			µA
I _{CC}		V _I = V _{CC} or GND, I _O = 0	3.6 V	10			µA
ΔI _{CC}		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V	750			µA
C _i	Control inputs	V _I = V _{CC} or GND	3.3 V	3.5			pF
	Data inputs			3.5			
C _O	Outputs	V _O = V _{CC} or GND	3.3 V	5.5			pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	1.3	5.3	1	3.2	3.1		1.1	2.8	ns
t _{en}	\overline{OE}	Y	1.4	6.4	1	4.1	4.3		1	3.5	ns
t _{dis}	\overline{OE}	Y	1.8	5.9	1	3.4	4		1.4	4	ns

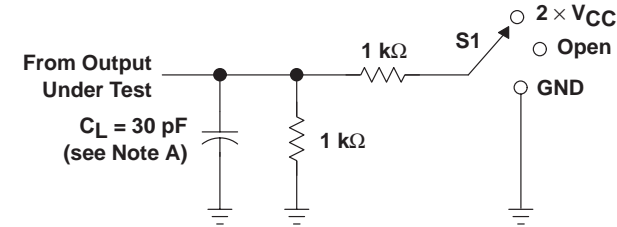
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
				TYP	TYP	TYP	
C _{pd}	Power dissipation capacitance per gate	Outputs enabled	C _L = 0, f = 10 MHz	15	17	19	pF
		Outputs disabled		2	2	3	



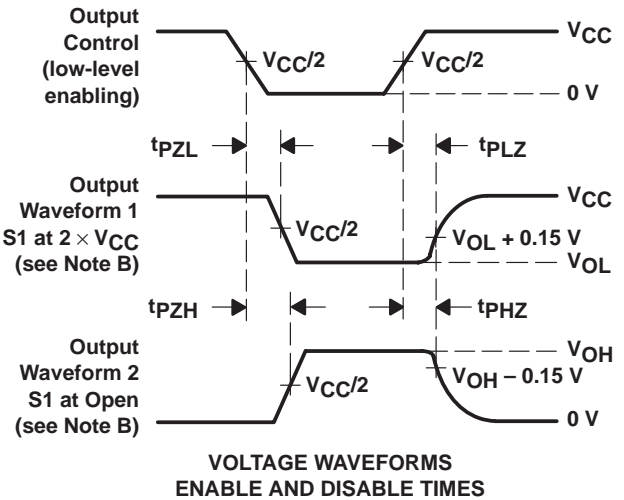
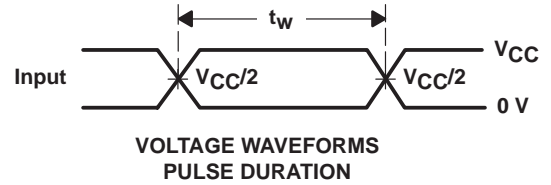
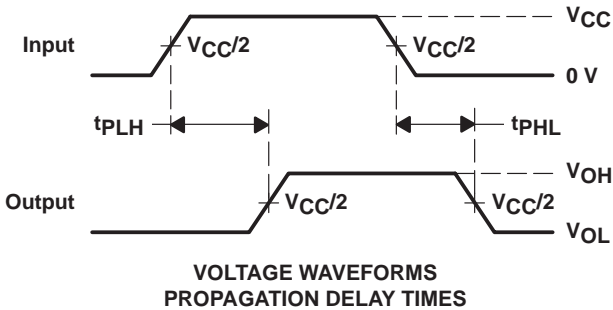
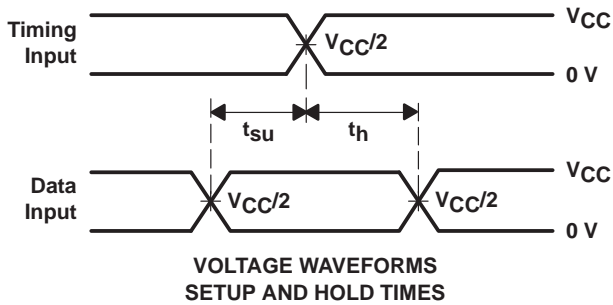
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PARAMETER MEASUREMENT INFORMATION
 $V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$



LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O = 50\ \Omega$, $t_r \leq 2\text{ ns}$, $t_f \leq 2\text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

SN74ALVC125

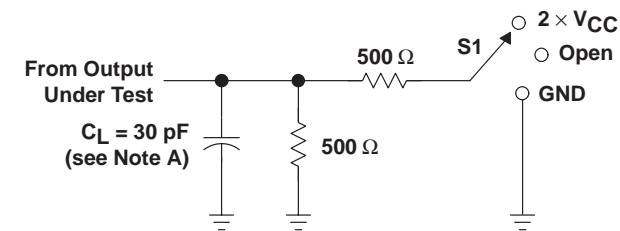
QUADRUPLE BUS BUFFER GATE

WITH 3-STATE OUTPUTS

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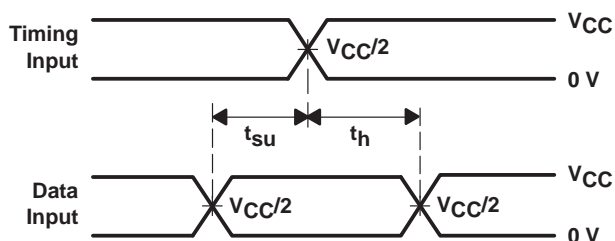
PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$$

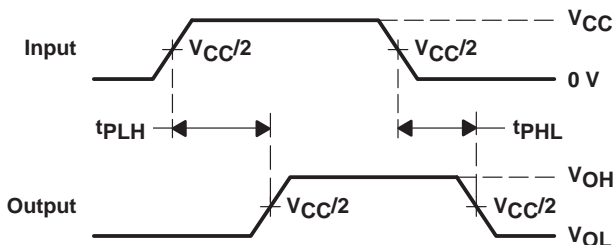


LOAD CIRCUIT

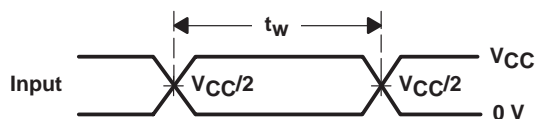
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 $\times V_{CC}$
t_{PHZ}/t_{PHZ}	GND



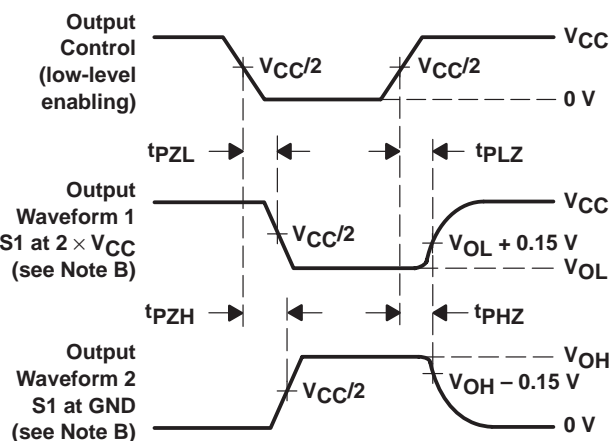
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

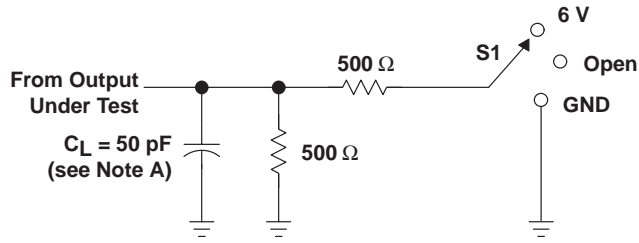


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

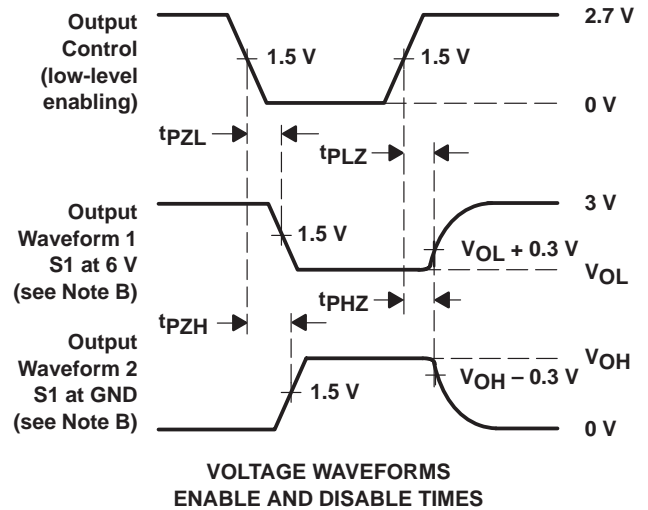
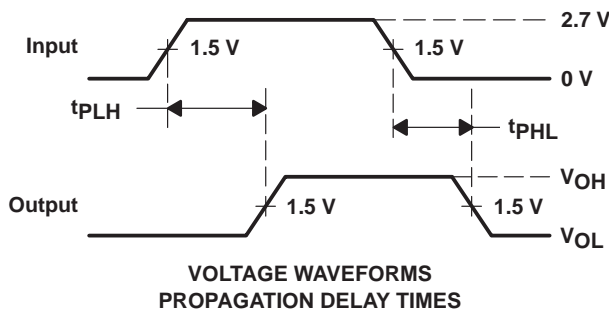
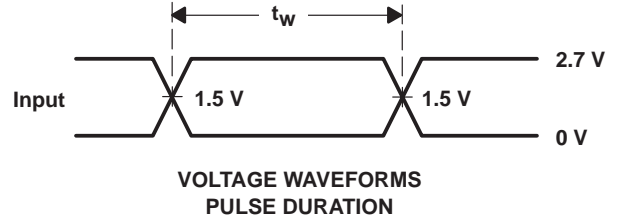
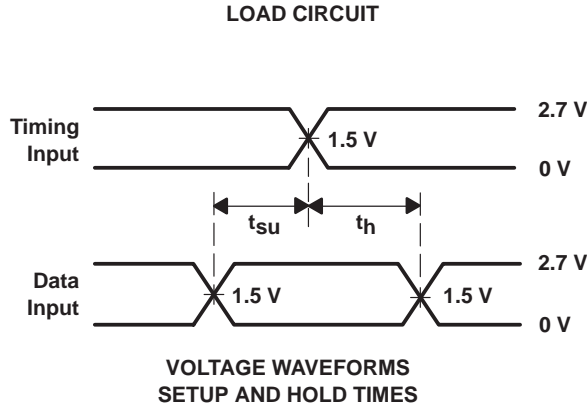
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
 $V_{CC} = 2.7\text{ V}$ AND $3.3\text{ V} \pm 0.3\text{ V}$



LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\text{ }\Omega$, $t_r \leq 2.5\text{ ns}$, $t_f \leq 2.5\text{ ns}$.
 - The outputs are measured one at a time with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 3. Load Circuit and Voltage Waveforms

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